TrenchT4™ **Power MOSFET**

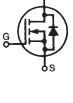
IXTA380N036T4-7

= 36V380A $1.0 m\Omega$

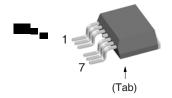
N-Channel Enhancement Mode Avalanche Rated



Symbol	Test Conditions	Maximum Ratings			
V _{DSS}	T _J = 25°C to 175°C	36	V		
V_{DGR}	$T_J = 25^{\circ}\text{C to } 175^{\circ}\text{C}, R_{GS} = 1\text{M}\Omega$	36	V		
V _{GSM}	Transient	±15	V		
I _{D25}	T _c = 25°C	380	Α		
LRMS	Lead Current Limit, RMS	160	Α		
I _{DM}	$T_{\rm C} = 25^{\circ}$ C, Pulse Width Limited by $T_{\rm JM}$	830	Α		
I _A	T _C = 25°C	190	A		
E _{as}	$T_{c} = 25^{\circ}C$	1.4	J		
$\overline{P_{D}}$	T _C = 25°C	480	W		
T _J		-55 +175	°C		
T_{JM}		175	°C		
T _{stg}		-55 +175	°C		
T _L	Maximum Lead Temperature for Soldering	g 300	°C		
T _{SOLD}	1.6 mm (0.062in.) from Case for 10s	260	°C		
F _c	Mounting Force	10.65 / 2.214.6	N/lb		
Weight		3.0	g		



TO-263 (7-lead)



Pins: 1 - Gate 2, 3, 5, 6, 7 - Source 4 (Tab) - Drain

Features

- International Standard Package
- 175°C Operating Temperature
- High Current Handling Capability
- Avalanche Rated
- Low R_{DS(on)}

Advantages

- Easy to Mount
- Space Savings
- High Power Density

Applications

- DC-DC Converts & Off-Line UPS
- High Current Switching Applications
- Primary-Side Switch

Symbol $(T_J = 25^{\circ}C$	Test Conditions Unless Otherwise Specified)	Chara Min.	acterist Typ.		
BV _{DSS}	V_{GS} = 0V, I_D = 250 μ A	36			V
V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	2.0		4.0	V
I _{GSS}	$V_{GS} = \pm 15V, V_{DS} = 0V$			±200	nA
I _{DSS}	$V_{DS} = V_{DSS}, V_{GS} = 0V$			10	μА
	$T_J = 150^{\circ}C$;		750	μΑ
R _{DS(on)}	$V_{GS} = 10V$, $I_{D} = 100A$, Note 1			1.0	mΩ



Symbo		acteristic	
$(1_{J} = 25)$	5°C, Unless Otherwise Specified) Min.	Тур.	Max.
\mathbf{g}_{fs}	$V_{DS} = 10V, I_{D} = 60A, \text{ Note 1}$ 105	175	S
R_{Gi}	Gate Input Resistance	1.0	Ω
C _{iss})	13.4	nF
\mathbf{C}_{oss}	$V_{GS} = 0V, V_{DS} = 25V, f = 1MHz$	2400	pF
\mathbf{C}_{rss}	J	1650	pF
t _{d(on)}	Pagistive Switching Times	36	ns
t _r	Resistive Switching Times $V_{GS} = 10V, V_{DS} = 0.5 \cdot V_{DSS}, I_{D} = 0.5 \cdot I_{D25}$	78	ns
$\mathbf{t}_{d(off)}$	$R_{G} = 5\Omega$ (External)	125	ns
t _f) G - (80	ns
Q _{g(on)}		260	nC
Q _{gs}	$V_{GS} = 10V, V_{DS} = 0.5 \cdot V_{DSS}, I_{D} = 0.5 \cdot I_{D25}$	60	nC
\mathbf{Q}_{gd}	J	92	nC
R _{thJC}			0.31 °C/W

Source-Drain Diode

Symbol $(T_J = 25^{\circ}C, U)$		hara Iin.	cteristic Typ.	Values Max.	
I _s	$V_{GS} = 0V$			380	Α
I _{SM}	Repetitive, Pulse width limited by T_{JM}			1520	Α
V_{SD}	$I_F = 100A, V_{GS} = 0V, \text{ Note 1}$			1.4	V
t _{rr}	$I_{\rm F} = 150 {\rm A}, V_{\rm GS} = 0 {\rm V}$		54		ns
I _{RM}	-di/dt = 100A/μs		2.6		Α
$Q_{_{\mathrm{RM}}}$	$V_R = 30V$		70		nC

Note 1: Pulse test, $t \le 300\mu s$, duty cycle, $d \le 2\%$.

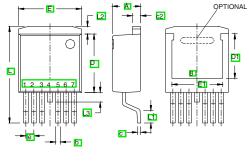
ADVANCE TECHNICAL INFORMATION

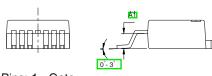
The product presented herein is under development. The Technical Specifications offered are derived from a subjective evaluation of the design, based upon prior knowledge and experience, and constitute a "considered reflection" of the anticipated result. IXYS reserves the right to change limits, test conditions, and dimensions without notice.



IXTA380N036T4-7

TO-263 (7-lead) (IXTA..7) Outline





Pins: 1 - Gate
2, 3, 5 , 6 , 7 - Source
4 - Drain

SYM	INCHES		MILLIMETER		
2114	MIN	MAX	MIN	MAX	
А	.170	.185	4.30	4.70	
A 1	.085	.104	2.15	2.65	
Ь	0 9 9	.035	0.65	0.90	
С	.016	.024	0.40	0.60	
c2	.049	.055	1.25	1.40	
D	.355	.370	9.00	9.40	
D1	.272	.280	6.90	7.10	
E	.386 .386	.402	9.80	10.20	
E 1	.311	.319	7.90	8.10	
е	.050 BSC		1.27BSC		
L	5	.614	15.00	15.60	
L1	.091	.110	2,30	2,80	
L2	.039	.059	1.00	1.50	
L3	.000	.059	0.00	1.50	

